IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

REVOCATION OF POWER OF ATTORNEY, NEW POWER OF ATTORNEY BY ASSIGNEE AND CHANGE OF CORRESPONDENCE ADDRESS

Sir:

Assignee hereby revokes all powers of attorney previously granted with respect to the patent applications identified in Appendix A, and appoints the firm of Myers Bigel Sibley & Sajovec:

Customer No. 20792

as its attorney, with full power of substitution and revocation to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all communications as follows:

Customer No. 20792

Myers Bigel Sibley & Sajovec, P.A. P. O. Box 37428 Raleigh, North Carolina 27627 Telephone: (919) 854-1400 Facsimile: (919) 854-1401

Assignee hereby elects under 37 C.F.R. § 3.71 to prosecute the patent applications listed in Appendix A.

The undersigned Assignee hereby certifies that Samsung Electronics Co., Ltd. is the assignee of the entire right, title, and interest in the patent applications identified in Appendix A by virtue of a chain of title from the inventor(s) of the patents or patent applications identified to Renesas Technology Corp. and then to the current assignee as shown in Appendix A.

The documents in the chain of title of the patent application identified above have been reviewed and, to the best of undersigned's knowledge and belief, title is in the assignee identified above.

The undersigned (whose title is supplied below) is empowered to sign this certificate on behalf of the Assignee.

I hereby declare that all statements made herein of my own knowledge are true, and that all statements made on information and belief are believed to be true; and further, that these statements are made with the knowledge that willful false statements, and the like so made, are punishable by fine or imprisonment, or both, under Section 1001, Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

Samsung Electronics Co., Ltd.

By:

Jeens Jack Kong Jeong-Tack Kong

Title: Senior Vice President of IP Team

Date: July 1, 2008

08/841612 5,8	rateiit 140.	Filing Date	Title of Patent
_	5,870,218	04/30/1997	Non-volatile Semiconductor Memory Device Which Stores Multi-Value Information
09/096457 5,9	5,982.667	96/11/1008	Non-volatile Semiconductor Memory Device For Storing Multivalue Information By Controlling Erase And Plural Write States of Each Memory Cell
09/339960 6,1	6,181,603	06/25/1999	Non-volatile Semiconductor Memory Device Having Plural Memory Cells Which Store Multi-Value Information
09/715106 6,3	6,396,736	11/26/2000	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
10/154853 6,7	6,771,537	05/28/2002	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
10/832311 7,0	7,031,187	April 27, 2004	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
11/332206 7,2	7,245,532	January 17, 2006	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
11/595880		November 13, 2006	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information

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12/11/918		May 9, 2008	Nonvolatile Semiconductor Memory Device Which Stores Multi-Value Information
07/704739	5,300,802	May 20, 1991	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/179960	5,407,853	January 11, 1994	Method of Making Semiconductor Integrated Circuit Device Having Single-Element Typc Non-Volatile Memory Elements
08/422941	5,656,839	April 17, 1995	Semiconductor Integrated Circuit Device Having Single-Element Type Nonvolatile Memory Elements
08/422940	5,629,541	April 17, 1995	Semiconductor Memory Device Constituted by Single Transistor Type Non-volatile Cells and Facilitated for Both Electrical Erasing and Writing of Data
08/451268	5,656,522	May 30, 1995	Method of Manufacturing a Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/885184	5,904,518	June 30, 1997	Method of Manufacturing a Semiconductor IC Device Having Single Transistor Type Nonvolatile Memory Cells
09/282204	6,255,690	March 31, 1999	Non-volatile Semiconductor Memory Device
09/873451	6,451,643	June 5, 2001	Method of Manufacturing a Semiconductor Device Having Non- volatile Memory Cell Portion with

			Single Transistor Type Memory Cells and Peripheral Portion with MISFETs
10/164626	6,777,282	June 10, 2002	Method of Manufacturing a Semiconductor Memory Device Having a Memory Cell Portion Including MISFETs With a Floating Gate and a Peripheral Circuit Portion With MISFETs
10/819205	6,960501	April 7, 2004	Method of Manufacturing a Semiconductor Memory Device Having a Non-volatile Memory Cell Portion with Single MISFET Transistor Type Memory Cells and a Peripheral Circuit Portion with MISFETs
11/220723	7,071,050	September 8, 2005	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
11/393774		March 31, 2006	Semiconductor Integrated Circuit Device Having Single-Element Type Non-volatile Memory Elements
08/913338	5,978,941	September 11, 1997	Semiconductor Memory Device Having Deterioration Determining Function
09/432389	6,223,311	November 2, 1999	Semiconductor Memory Device Having Deterioration Determining Function
09/794073	6,694,460	February 28, 2001	Semiconductor Memory Device Having Deterioration Determining Function